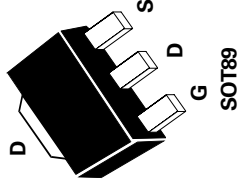


**SOT89 PNP SILICON PLANAR
HIGH VOLTAGE TRANSISTOR**

ISSUE 3 - NOVEMBER 1995

FCX596



PARTMARKING DETAIL - P96

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-220	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.3	A
Base Current	I_B	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-220		$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200		$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}		-100	$V_{CE} = -200V$
Emitter Cut-Off Current	I_{EBO}		-100	$V_{EB} = -4V$
Collector-Emitter Cut-Off Current	I_{CES}		-100	$V_{CES} = -200V$
Saturation Voltages	$V_{CE(sat)}$	-0.2		$I_C = -100mA, I_B = -10mA$
		-0.35		$I_C = -250mA, I_B = -25mA^*$
	$V_{BE(sat)}$		-1.0	$I_C = -250mA, I_B = -25mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-0.9	$I_C = -250mA, V_{CE} = -10V^*$
Static Forward Current Transfer Ratio	h_{FE}	100		$I_C = -1mA, V_{CE} = -10V$
		100		$I_C = -100mA, V_{CE} = -10V^*$
		85	300	$I_C = -250mA, V_{CE} = -10V^*$
		35		$I_C = -400mA, V_{CE} = -10V,$
Transition Frequency	f_T	150		$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$
Output Capacitance	C_{obo}		10	$V_{CE} = -10V, f = 1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$.
For typical Characteristics graphs see FMMT596 datasheet.